



Contribution ID: 103

Type: Talk

【623】 A laser-ARPES study of LaNiO₃ thin films grown in-situ by sputter deposition

Wednesday 28 August 2019 14:30 (15 minutes)

Thin films of the transition-metal oxide LaNiO₃ (LNO) undergo a metal-insulator transition when their thickness is reduced to 2-3 unit cells. Here, we use a state-of-the-art laser-ARPES setup to map the electronic structure of LNO thin films with improved resolution. A series of high-quality films of thicknesses ranging from 19 to 2 unit cells is grown by sputter deposition and transferred in vacuo to the ARPES setup. Our measurements show an unchanged Fermi surface for all metallic samples. However, the peak width of the momentum distribution curve at the Fermi level progressively increases as the thickness is reduced. This suggests that the metal-insulator transition is driven by the increasing importance of interfacial scattering and a reduced inelastic mean free path.

Author: CAPPELLI, Edoardo (Université de Genève)

Co-authors: MCKEOWN WALKER, Siobhan (University of Geneva); Dr TAMAI, Anna (University of Geneva); Prof. GIBERT, Marta (University of Zürich); TRISCONE, Jean-Marc (Department of Quantum Matter Physics, University of Geneva, Switzerland); Prof. BAUMBERGER, Felix (University of Geneva); Dr YAIR BRUNO, Flavio (Complutense University of Madrid); Mr TROMP, Willem (University of Leiden)

Presenter: CAPPELLI, Edoardo (Université de Genève)

Session Classification: MaNEP: Correlations and topology in quantum matter

Track Classification: MaNEP Session: Correlations and topology in quantum matter